

Abstract

Process for producing semiconductor wafers with epitaxial layer deposited from the gas phase in a deposition chamber

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A process for producing semiconductor wafers with epitaxial layer deposited from the gas phase in a deposition chamber, comprising
the placement of a substrate wafer on a susceptor with circular perimeter by a robot,
10 where the robot moves the substrate wafer into a placement position and places it on the susceptor, with a corrective precept causing the center of the substrate wafer not to lie above the center of the susceptor in the placement position; and
the deposition of an epitaxial layer on the substrate wafer, wherein
a first number of substrate wafers having a specific resistance which falls within a first
15 range are moved into the placement position by the robot with a first corrective precept, and a second number of substrate wafers having a specific resistance which falls within a second range are moved into the placement position by the robot with a second corrective precept, where the first and second corrective precepts differ from one another.

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Drawing for the Abstract: Fig. 2